NCE N-Channel Enhancement Mode Power MOSFET

DESCRIPTION

The NCE3080K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

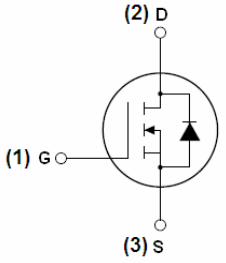
GENERAL FEATURES

- V_{DS} =30V,I_D =80A
  $R_{DS(ON)}$ < 6.5mΩ @ V_{GS}=10V
  $R_{DS(ON)}$ < 10mΩ @ V_{GS}=5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

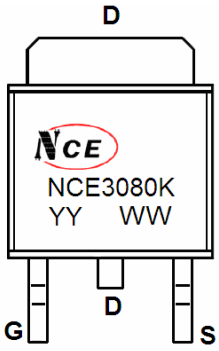
Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

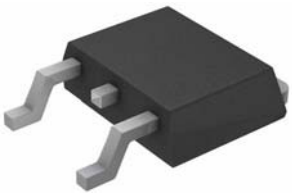
100% UIS TESTED!



Schematic diagram



Marking and pin Assignment



TO-252 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3080K	NCE3080K	TO-252	-	-	-

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	80	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	50	A
Pulsed Drain Current	I_{DM}	170	A
Maximum Power Dissipation	P_D	83	W
Derating factor		0.56	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	140	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case(Note 2)	$R_{\theta JC}$	1.8	℃/W

Electrical Characteristics (TA=25℃unless otherwise noted)

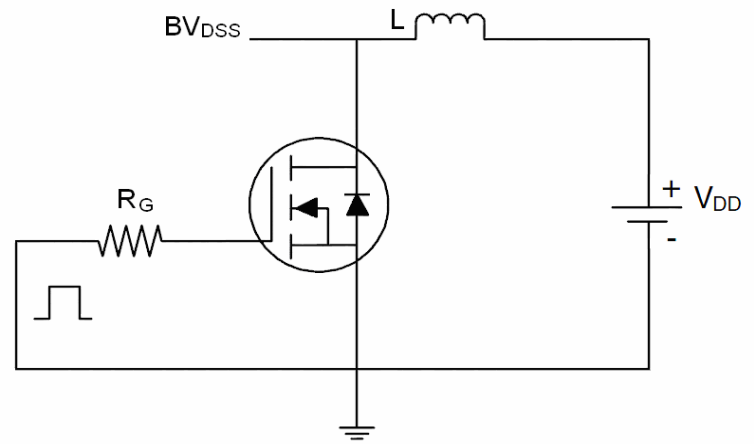
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1		3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A			6.5	mΩ
		V_{GS}=5V, I_D=24A			10	
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=24A	20			S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz		4700		PF
Output Capacitance	C_{oss}			500		PF
Reverse Transfer Capacitance	C_{rss}			345		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=30A V_{GS}=10V,R_{GEN}=2.7Ω		20		nS
Turn-on Rise Time	t_r			15		nS
Turn-Off Delay Time	$t_{d(off)}$			65		nS
Turn-Off Fall Time	t_f			10		nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=30A, V_{GS}=10V		51		nC
Gate-Source Charge	Q_{gs}			14		nC
Gate-Drain Charge	Q_{gd}			11		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=24A		0.85	1.2	V
Diode Forward Current (Note 2)	I_S				80	A
Reverse Recovery Time	t_{rr}	TJ = 25°C, IF = 80A di/dt = 100A/μs(Note3)		32	50	nS
Reverse Recovery Charge	Qrr			12	20	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

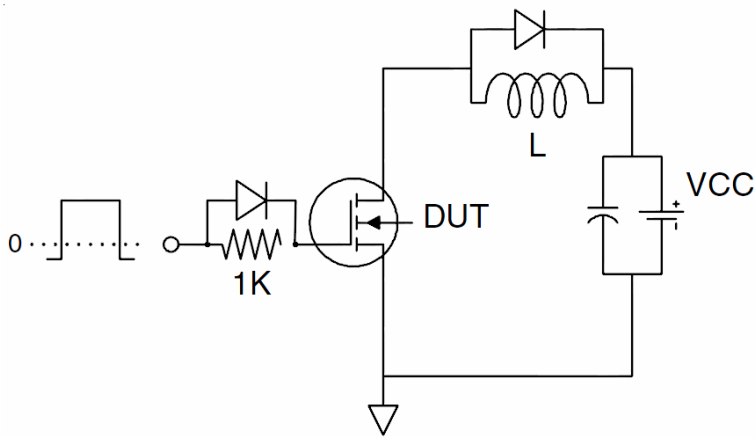
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition：Tj=25℃,V_{DD}=15V,V_G=10V,L=1mH,Rg=25Ω

Test circuit

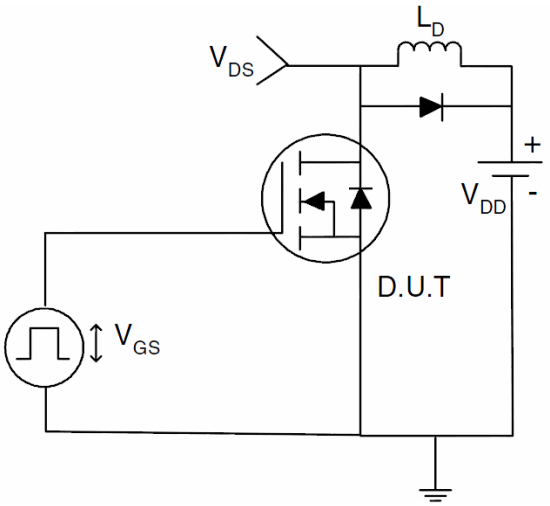
1）E_{AS} test Circuits



2）Gate charge test Circuit:



3）Switch Time Test Circuit：



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)

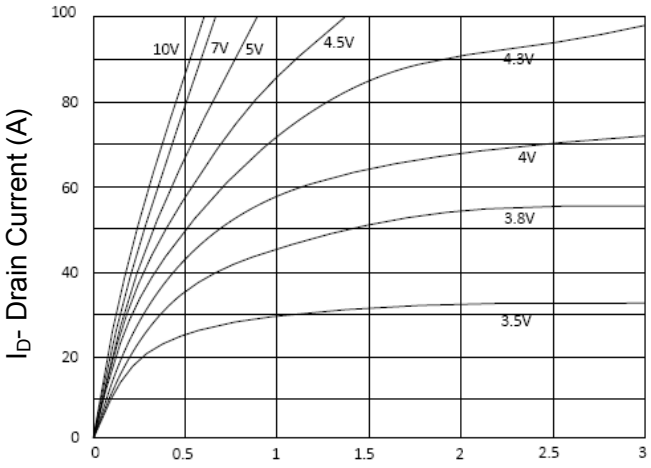


Figure 1 Output Characteristics

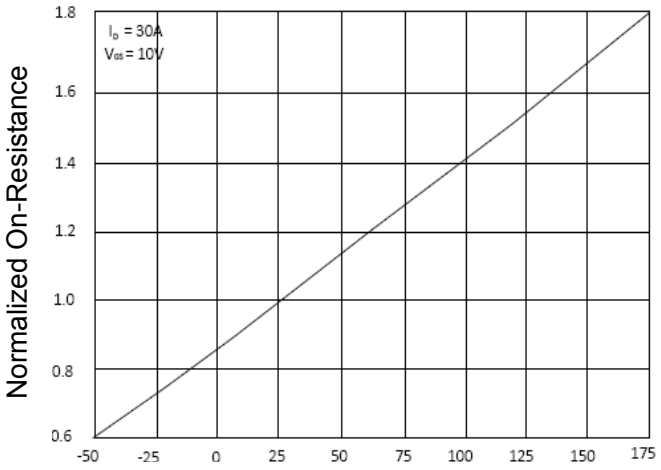


Figure 4 Rdson-JunctionTemperature

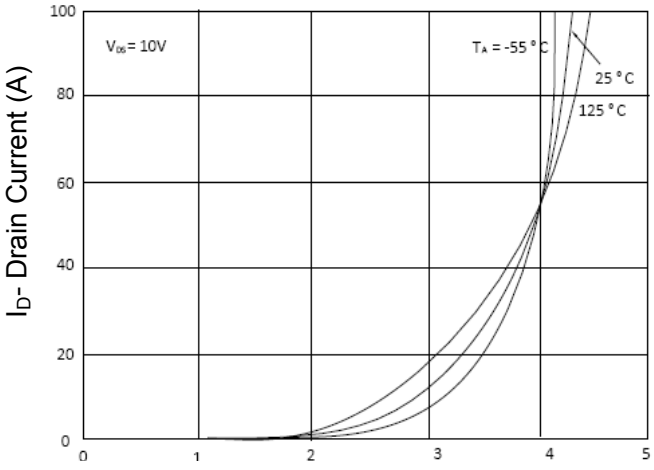


Figure 2 Transfer Characteristics

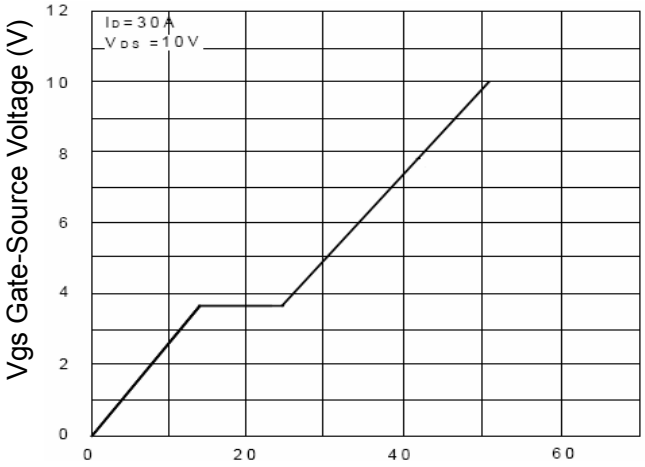


Figure 5 Gate Charge

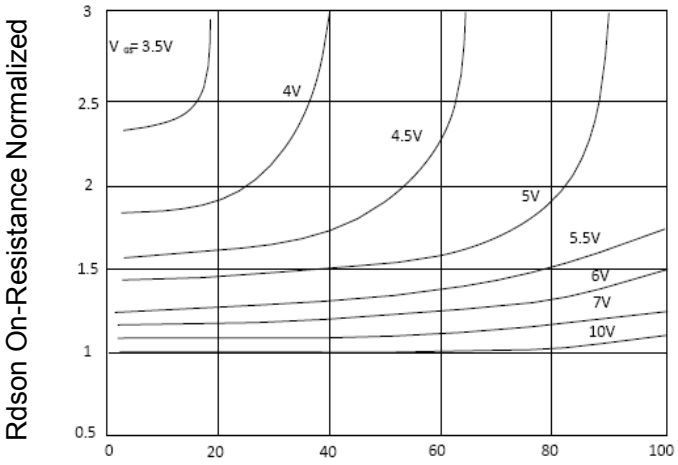


Figure 3 Rdson- Drain Current

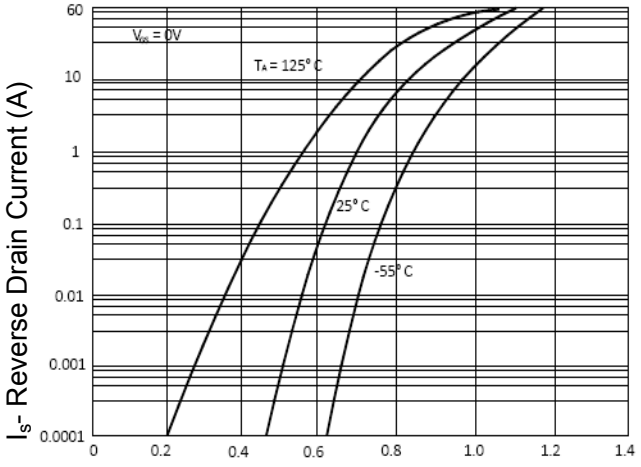


Figure 6 Source- Drain Diode Forward

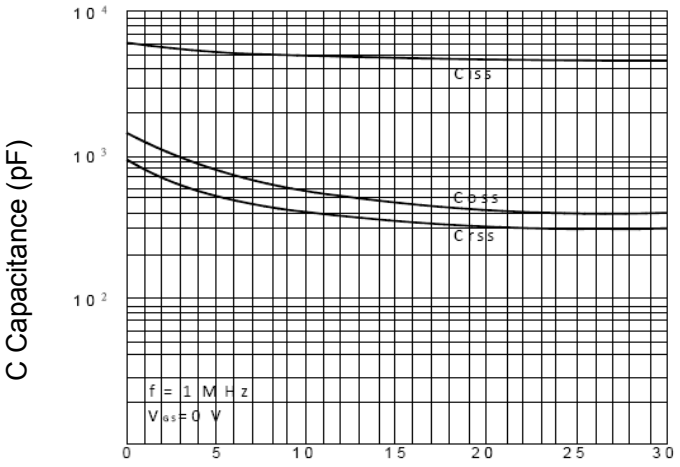


Figure 7 Capacitance vs Vds

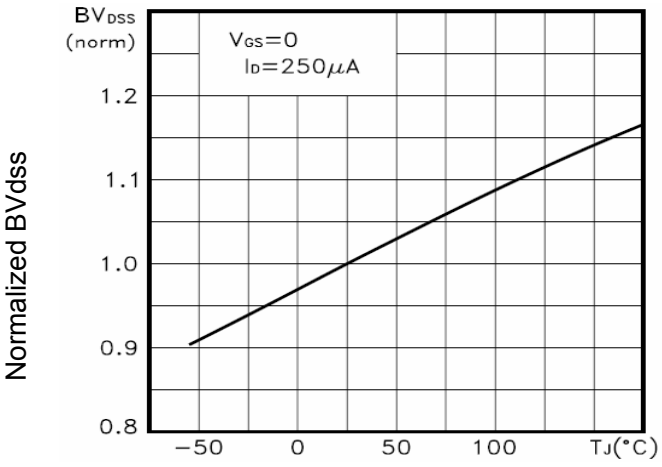


Figure 9 BV_{DSS} vs Junction Temperature

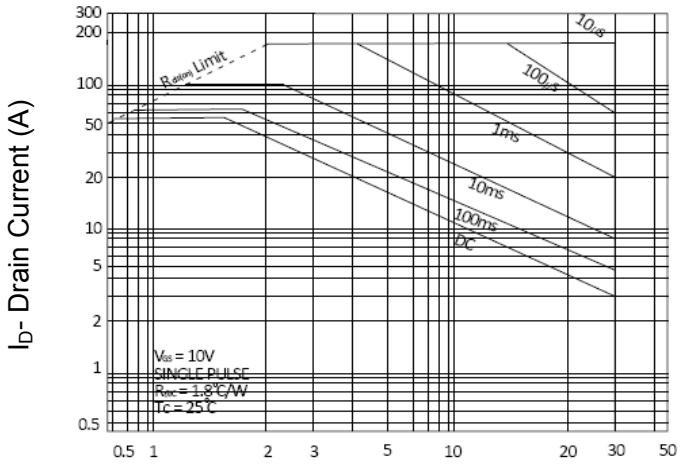


Figure 8 Safe Operation Area

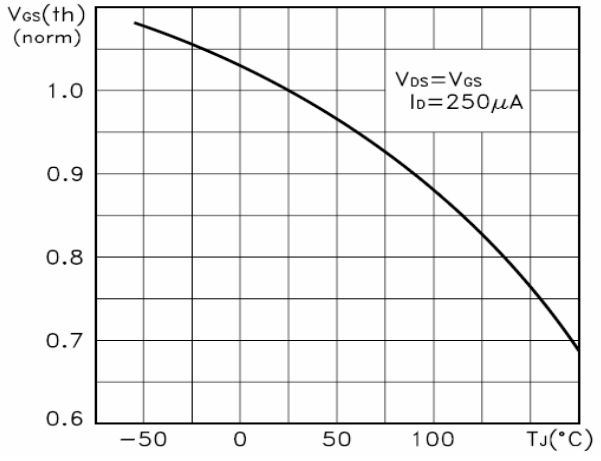


Figure 10 $V_{GS(th)}$ vs Junction Temperatur

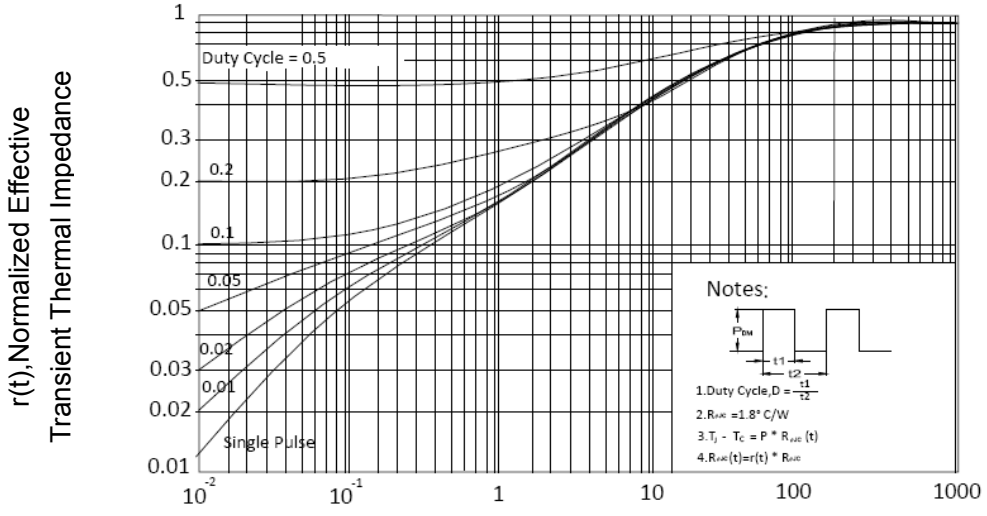
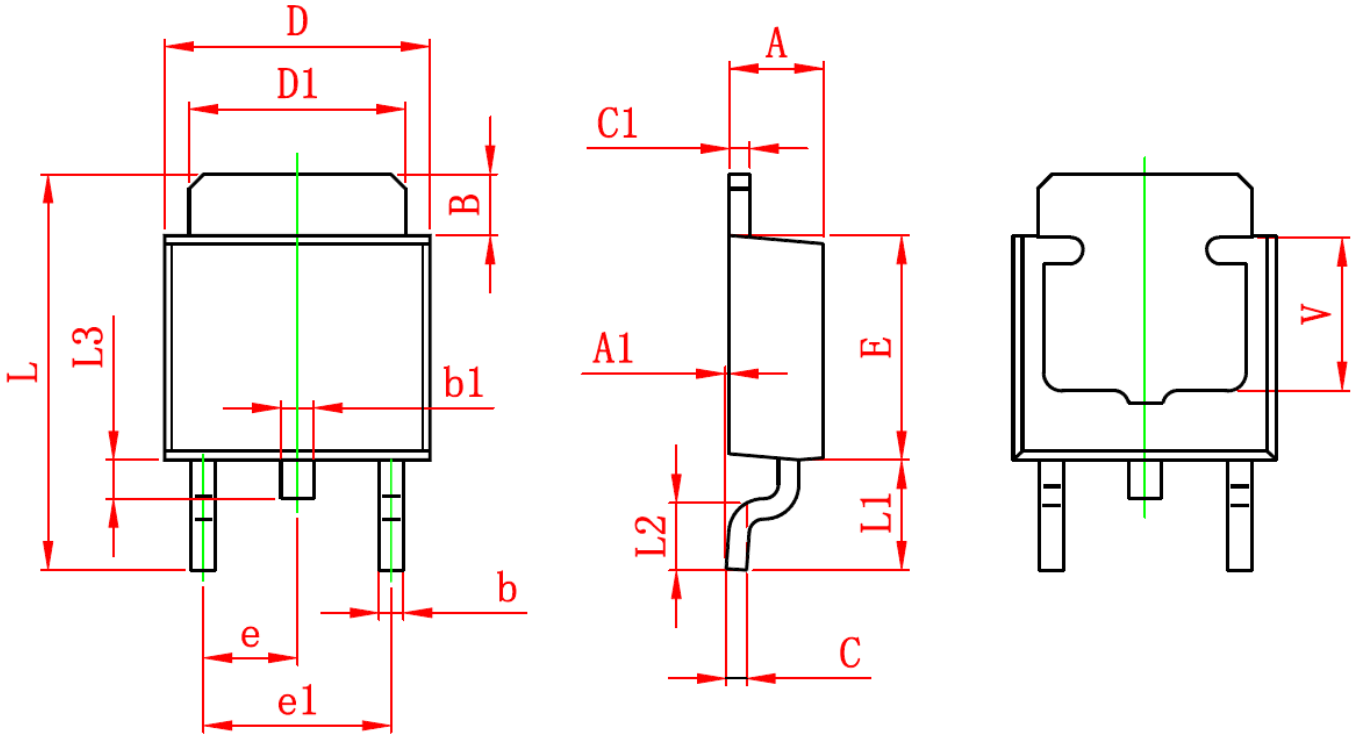


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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